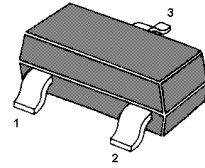


MMBTA63 / MMBTA64

PNP Silicon Epitaxial Planar Transistor

for general purpose application, darlington transistor



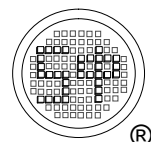
1.BASE 2.EMITTER 3.COLLECTOR
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

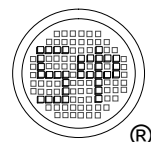
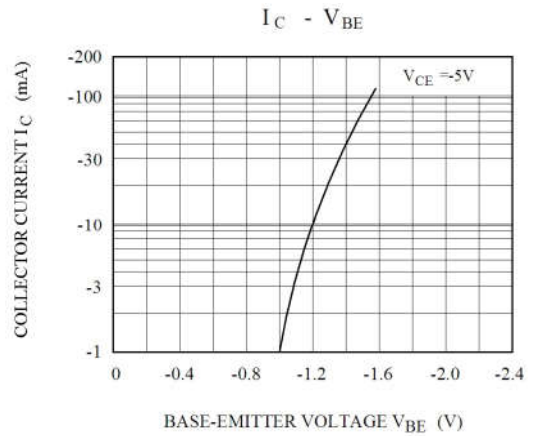
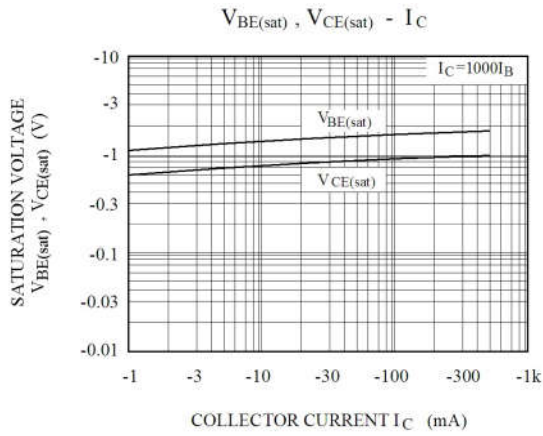
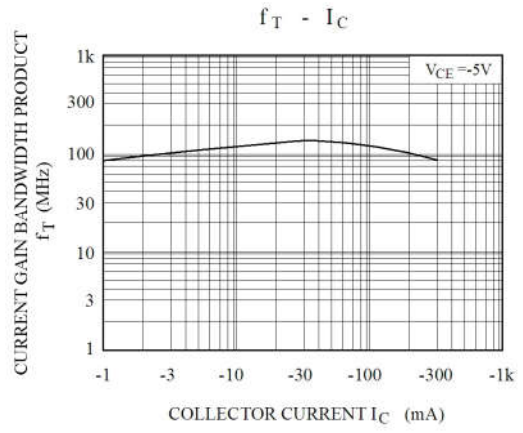
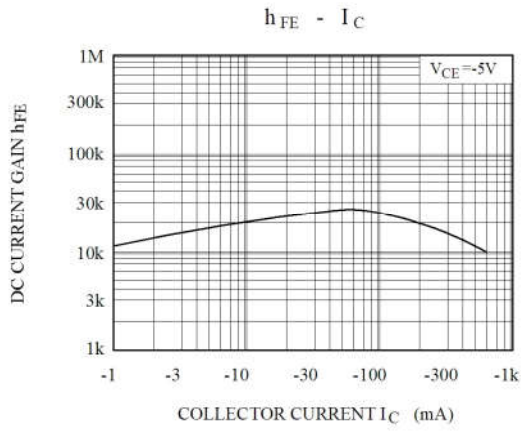
Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	30	V
Collector Emitter Voltage	$-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	10	V
Collector Current	$-I_C$	500	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain				
at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	MMBTA63	h_{FE}	5000	-
at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	MMBTA64	h_{FE}	10000	-
at $-V_{CE} = 5\text{ V}$, $-I_C = 100\text{ mA}$	MMBTA63	h_{FE}	10000	-
at $-V_{CE} = 5\text{ V}$, $-I_C = 100\text{ mA}$	MMBTA64	h_{FE}	20000	-
Collector Cutoff Current				
at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	100	nA
Emitter Cutoff Current				
at $-V_{EB} = 10\text{ V}$	$-I_{EBO}$	-	100	nA
Collector Emitter Breakdown Voltage				
at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CEO}$	30	-	V
Collector Emitter Saturation Voltage				
at $-I_C = 100\text{ mA}$, $-I_B = 0.1\text{ mA}$	$-V_{CE(sat)}$	-	1.5	V
Base Emitter On Voltage				
at $-V_{CE} = 5\text{ V}$, $-I_C = 100\text{ mA}$	$-V_{BE(on)}$	-	2	V
Transition Frequency				
at $-V_{CE} = 5\text{ V}$, $I_E = 10\text{ mA}$	f_T	125	-	MHz



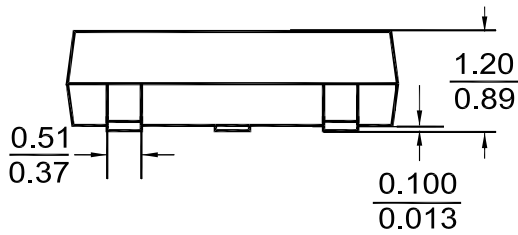
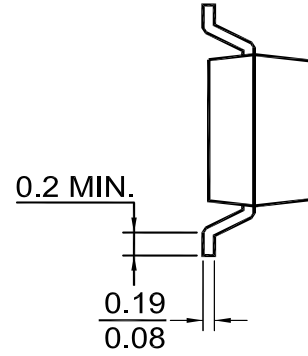
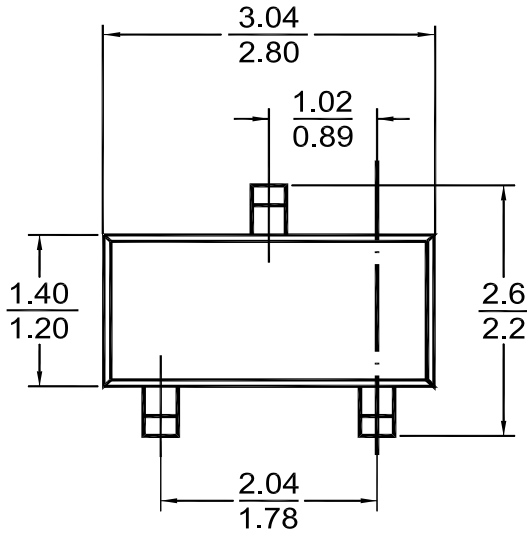
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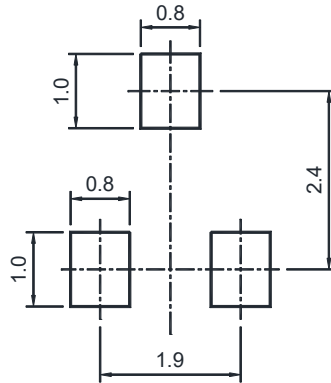
MMBTA63 / MMBTA64

Package Outline (Dimensions in mm)

SOT-23



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-23	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

